

## ABSTRACT

A silicon carbide product is disclosed which is characterized by having a surface with a metal impurity concentration of not more than  $1 \times 10^{11}$  (atoms/cm<sup>2</sup>). Also disclosed are a method for producing such a silicon carbide product and a method for cleaning a silicon carbide product. A silicon carbide having such a highly cleaned surface can be obtained by cleaning it with a hydrofluoric acid, a hydrochloric acid, or an aqueous solution containing a sulfuric acid and a hydrogen peroxide solution. The present invention provides a highly cleaned silicon carbide, and thus enables to produce a semiconductor device which is free from consideration on deterioration in characteristics caused by impurities. Further, when the silicon carbide is used in a unit for semiconductor production or the like, there is such an advantage that an object processed in the unit can be prevented from suffering an adverse affect of flying impurities.